

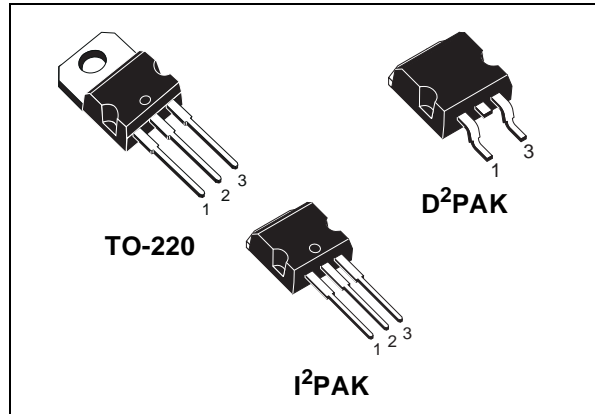


# STP40NF10 STB40NF10 - STB40NF10-1

N-CHANNEL 100V - 0.024Ω - 50A TO-220/D<sup>2</sup>PAK/I<sup>2</sup>PAK  
LOW GATE CHARGE STripFET™ II POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STP40NF10	100 V	< 0.028 Ω	50 A
STB40NF10	100 V	< 0.028 Ω	50 A
STB40NF10-1	100 V	< 0.028 Ω	50 A

- TYPICAL R<sub>DS(on)</sub> = 0.024Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION
- ADD SUFFIX "T4" FOR ORDERING IN TAPE & REEL



## DESCRIPTION

This Power MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency isolated DC-DC converters for Telecom and Computer application. It is also intended for any application with low gate charge drive requirements.

## APPLICATIONS

- HIGH-EFFICIENCY DC-DC CONVERTERS
- UPS AND MOTOR CONTROL

## ABSOLUTE MAXIMUM RATINGS

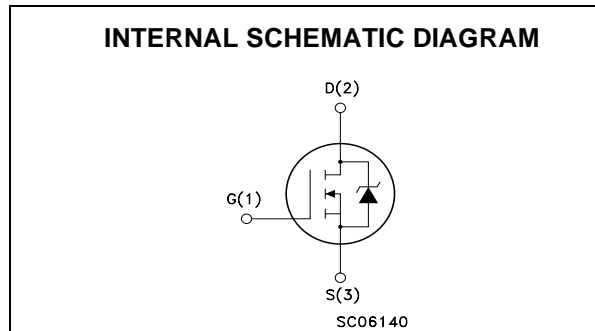
Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	100	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	100	V
V <sub>GS</sub>	Gate- source Voltage	± 20	V
I <sub>D</sub> (*)	Drain Current (continuous) at T <sub>C</sub> = 25°C	50	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	35	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	200	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	150	W
	Derating Factor	1	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	20	V/ns
E <sub>AS</sub> (2)	Single Pulse Avalanche Energy	150	mJ
T <sub>stg</sub>	Storage Temperature	- 55 to 175	°C
T <sub>j</sub>	Operating Junction Temperature		

(●) Pulse width limited by safe operating area

(\*) Limited by Package

(1) I<sub>SD</sub> ≤ 40A, di/dt ≤ 600A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

(2) Starting T<sub>j</sub> = 25°C, I<sub>D</sub> = 40A, V<sub>DD</sub> = 50V



## STP40NF10 - STB40NF10 - STB40NF10-1

### THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	1	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T <sub>I</sub>	Maximum Lead Temperature For Soldering Purpose	300	°C

### ELECTRICAL CHARACTERISTICS (T<sub>CASE</sub> = 25 °C UNLESS OTHERWISE SPECIFIED) OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	100			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20V			±100	nA

### ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2	2.8	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20 A		0.024	0.028	Ω

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (1)	Forward Transconductance	V <sub>DS</sub> = 25V, I <sub>D</sub> = 20 A		20		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		1780		pF
C <sub>oss</sub>	Output Capacitance			265		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			112		pF

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 50\text{ V}, I_D = 20\text{ A}$		28		ns
$t_r$	Rise Time	$R_G = 4.7\Omega, V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		63		ns
$Q_g$	Total Gate Charge	$V_{DD} = 80\text{ V}, I_D = 40\text{ A}, V_{GS} = 10\text{ V}$		60	80	nC
$Q_{gs}$	Gate-Source Charge			10		nC
$Q_{gd}$	Gate-Drain Charge			23		nC

**SWITCHING OFF**

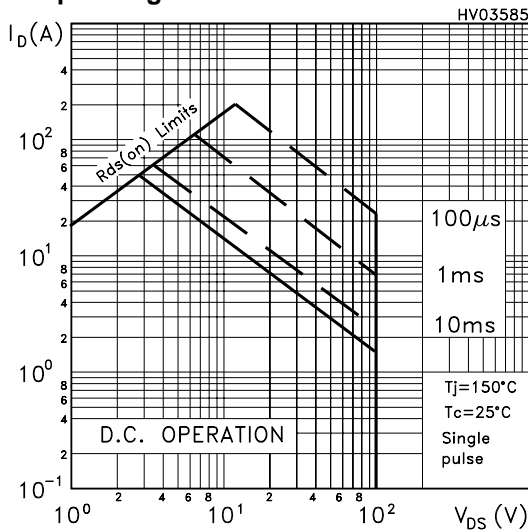
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 50\text{ V}, I_D = 20\text{ A},$		84		ns
$t_f$	Fall Time	$R_G = 4.7\Omega, V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		28		ns

**SOURCE DRAIN DIODE**

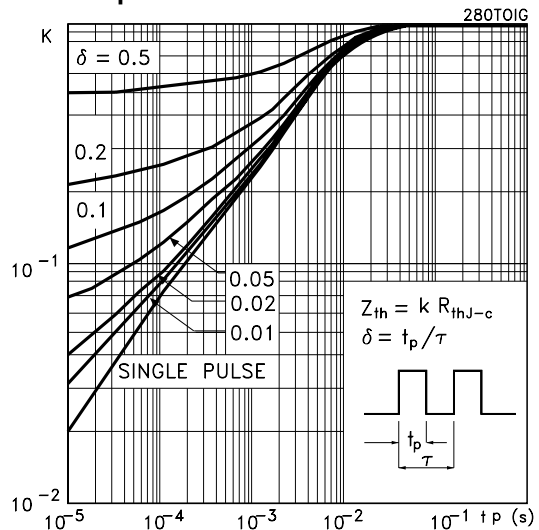
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				40	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				160	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 40\text{ A}, V_{GS} = 0$			1.3	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 40\text{ A}, di/dt = 100\text{ A}/\mu\text{s},$		114		ns
$Q_{rr}$	Reverse Recovery Charge	$V_{DD} = 25\text{ V}, T_j = 150^\circ\text{C}$		456		nC
$I_{RRM}$	Reverse Recovery Current	(see test circuit, Figure 5)		8		A

Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

**Safe Operating Area**

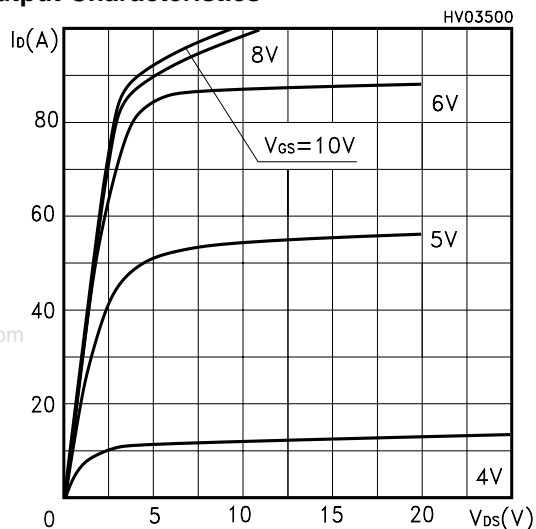


**Thermal Impedance**

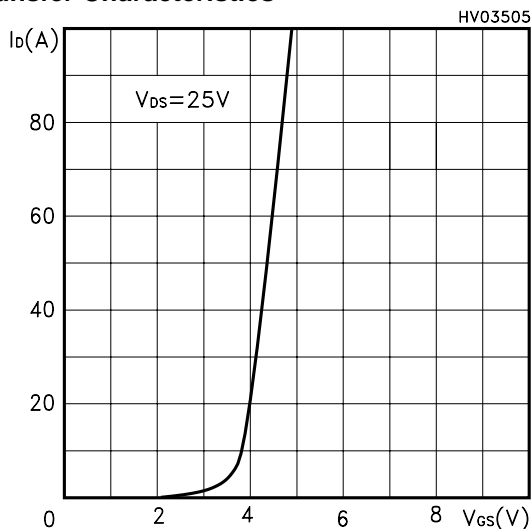


# STP40NF10 - STB40NF10 - STB40NF10-1

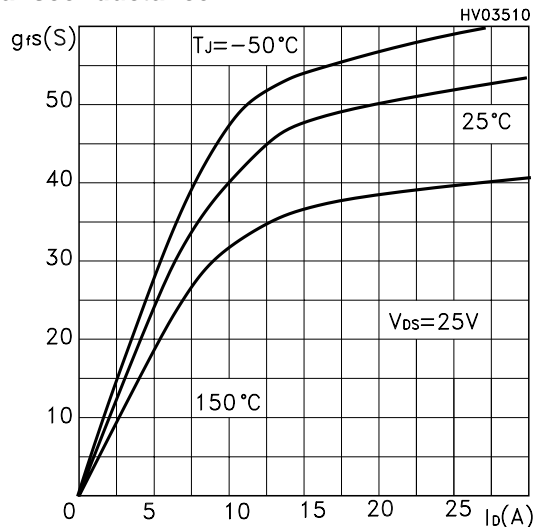
## Output Characteristics



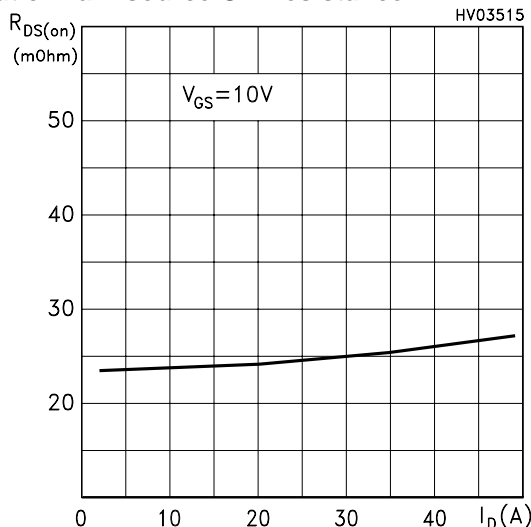
## Transfer Characteristics



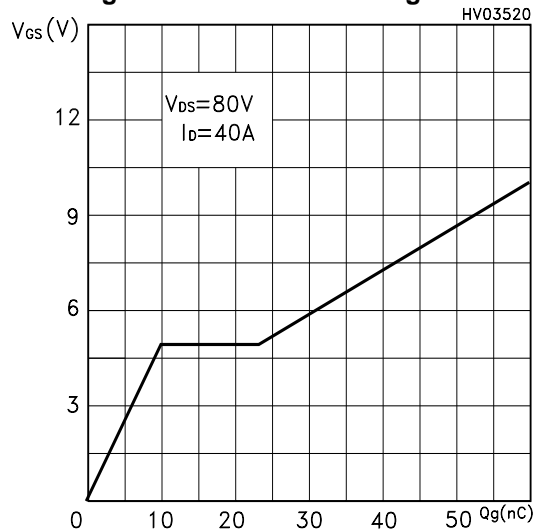
## Transconductance



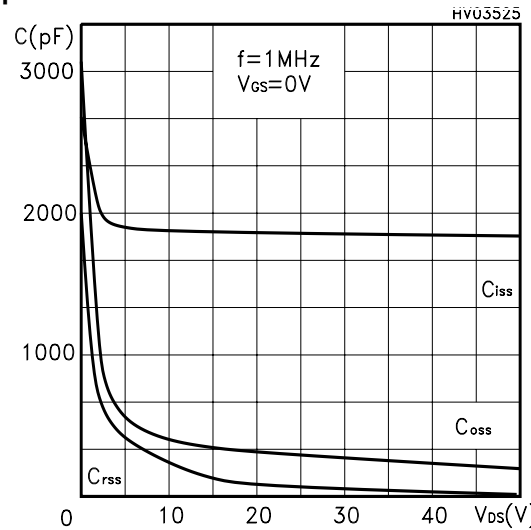
## Static Drain-source On Resistance



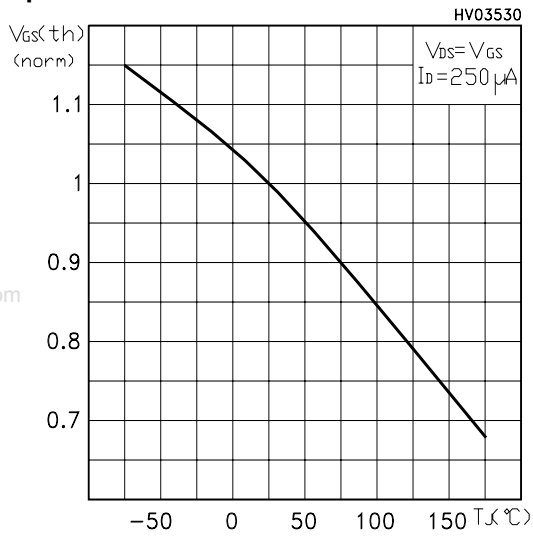
## Gate Charge vs Gate-source Voltage



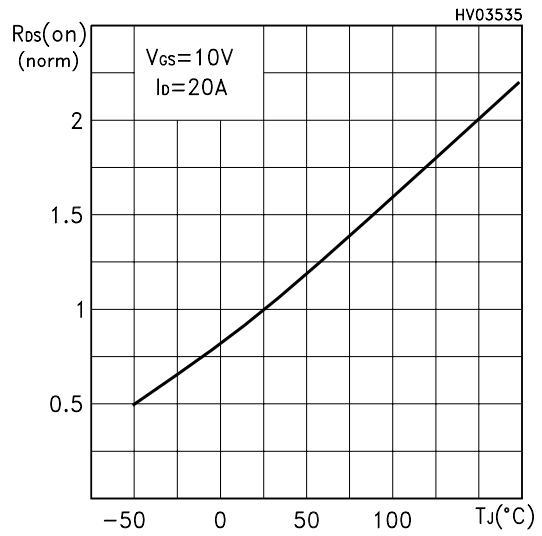
## Capacitance Variations



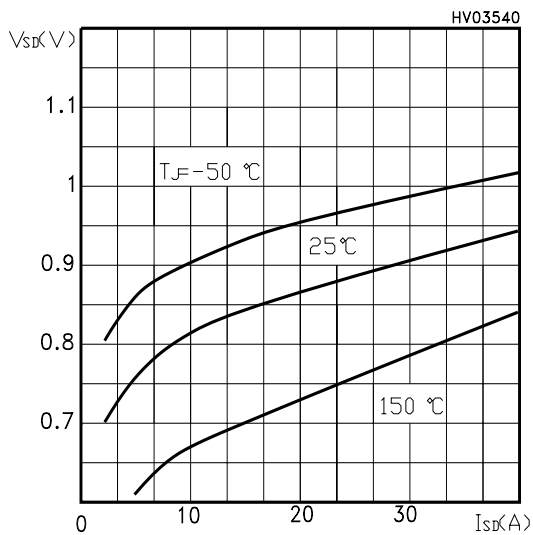
**Normalized Gate Threshold Voltage vs Temperature**



**Normalized On Resistance vs Temperature**



**Source-drain Diode Forward Characteristics**



**Normalized Drain-Source Breakdown vs Temperature**

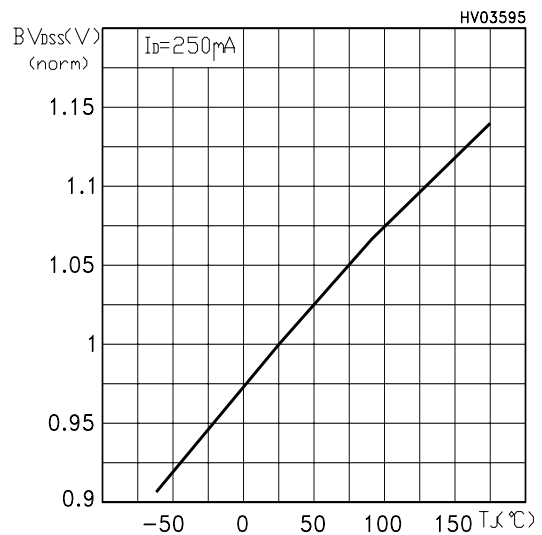


Fig. 1: Unclamped Inductive Load Test Circuit

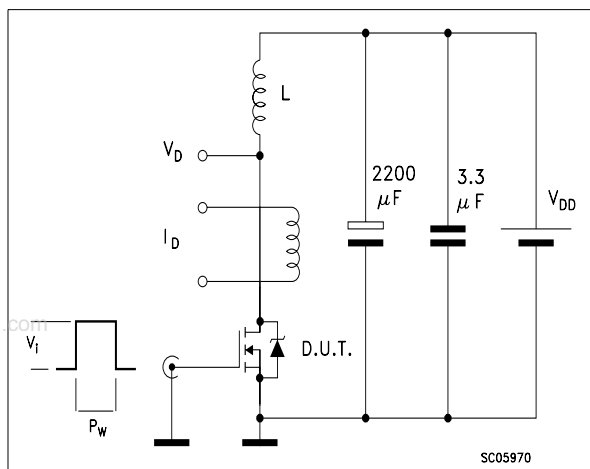


Fig. 2: Unclamped Inductive Waveform



Fig. 3: Switching Times Test Circuit For Resistive Load

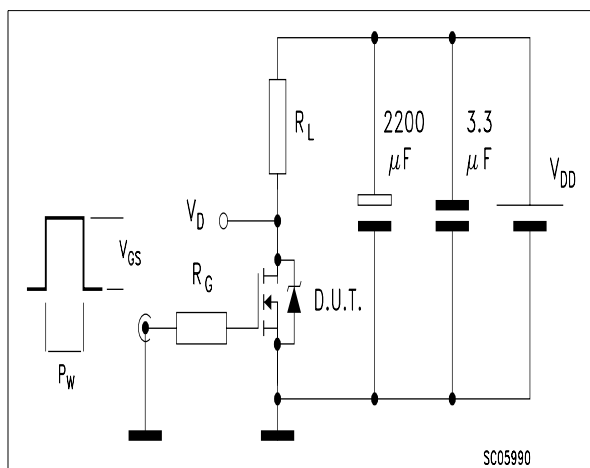


Fig. 4: Gate Charge test Circuit

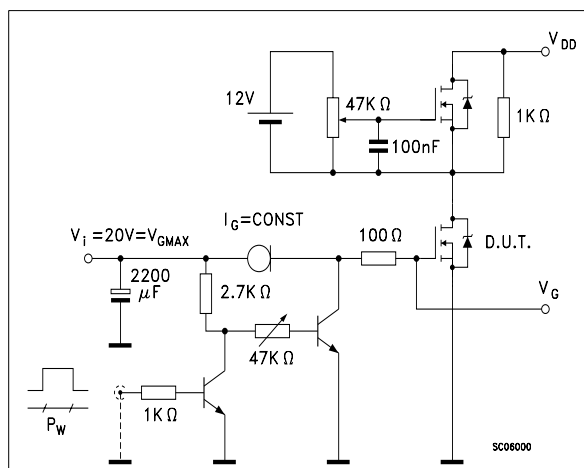
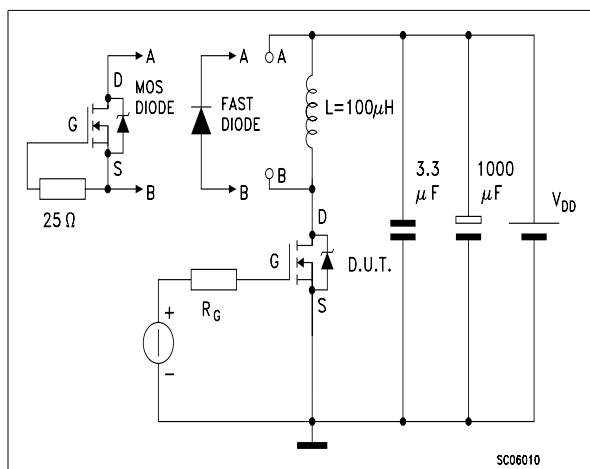
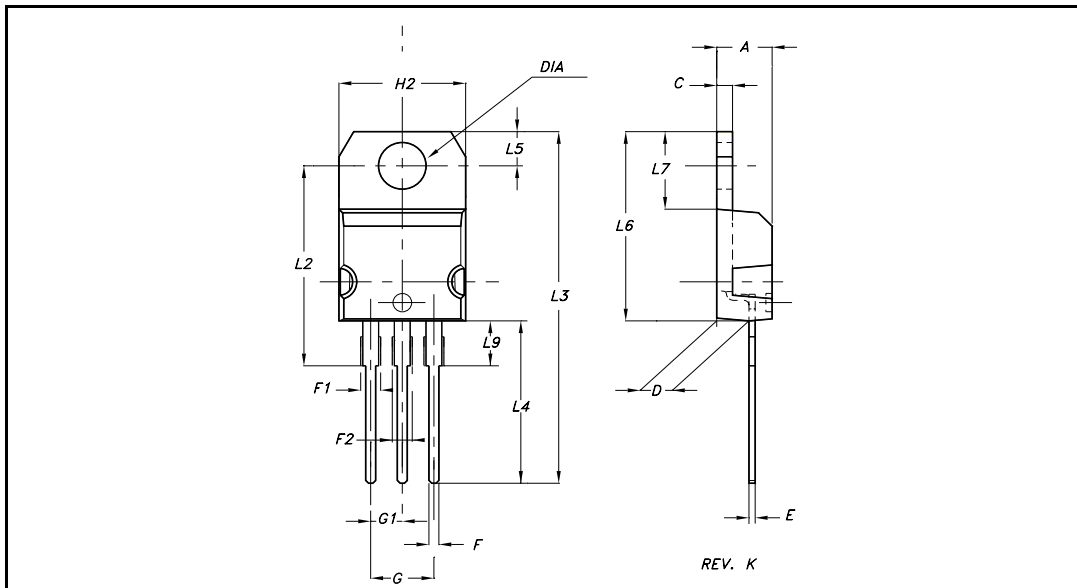


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



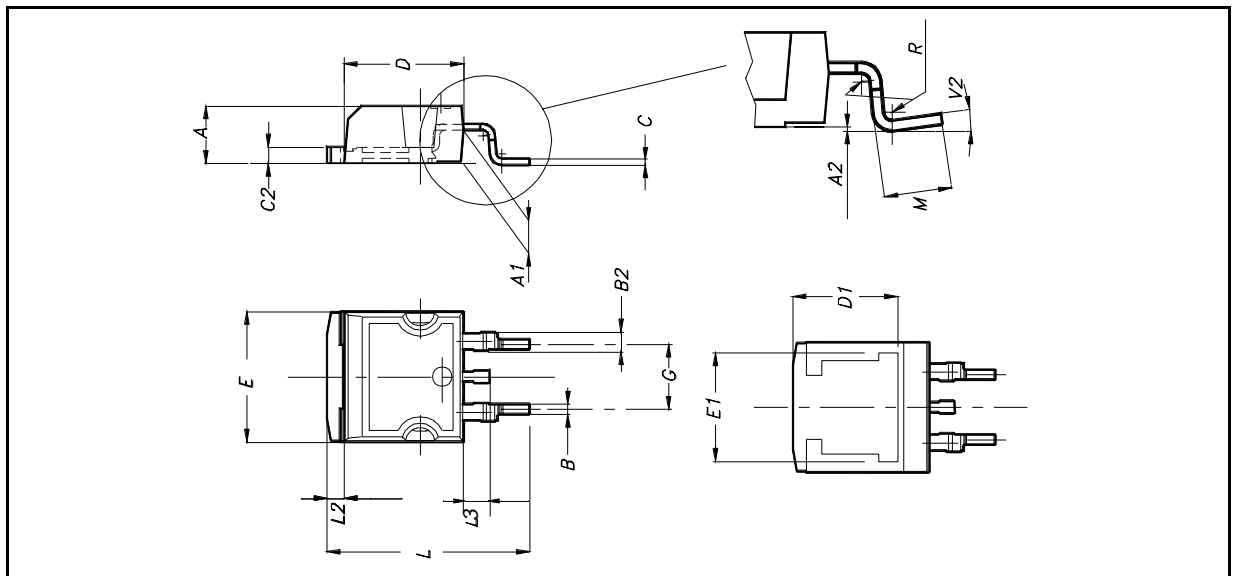
**TO-220 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.066
F2	1.14		1.70	0.044		0.066
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10		10.40	0.393		0.409
L2		16.40			0.645	
L3		28.90			1.137	
L4	13		14	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.259
L9	3.50		3.93	0.137		0.154
DIA	3.75		3.85	0.147		0.151



**D<sup>2</sup>PAK MECHANICAL DATA**

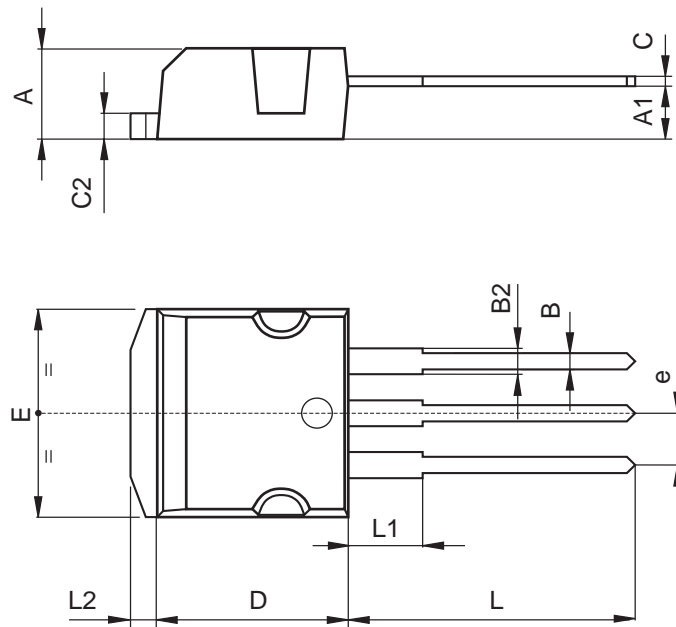
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°			





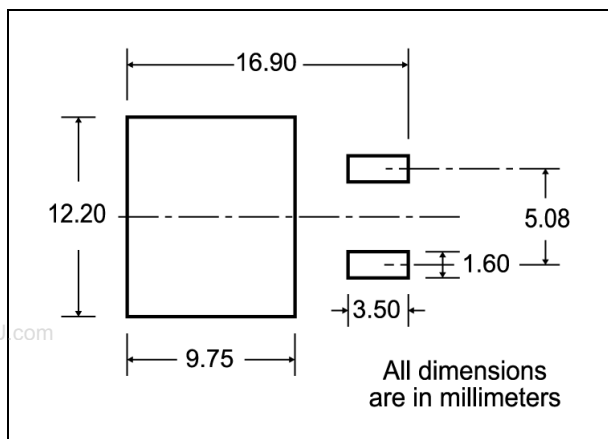
TO-262 (I<sup>2</sup>PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
e	2.4		2.7	0.094		0.106
E	10		10.4	0.393		0.409
L	13.1		13.6	0.515		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.4	0.050		0.055

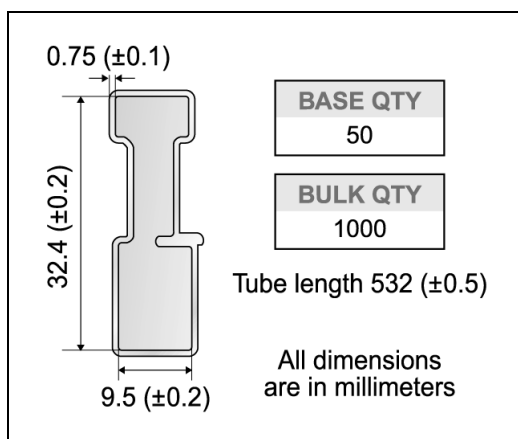


P011P5/E

**D<sup>2</sup>PAK FOOTPRINT**



**TUBE SHIPMENT (no suffix)\***



**TAPE AND REEL SHIPMENT (suffix "T4")\***

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

TOP COVER TAPE

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

FEED DIRECTION

Bending radius R min.

\* on sales type



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